

ABSTRACT OF THE DISCLOSURE

[0037] Non-volatile memory such as flash EEPROM has memory cells that may be programmed in parallel using a self-limiting programming technique. Individual cells have charge storage units that may be charged by hot electrons in a self-limiting manner. As the charge storage unit reaches the required level of charge, hot electrons are no longer generated, or are generated in reduced number. The level of charge at which hot electron generation stops is determined by the voltage applied to the cell. Thus, several cells may be programmed in parallel, each self-limiting at a charge level corresponding to the voltage applied.